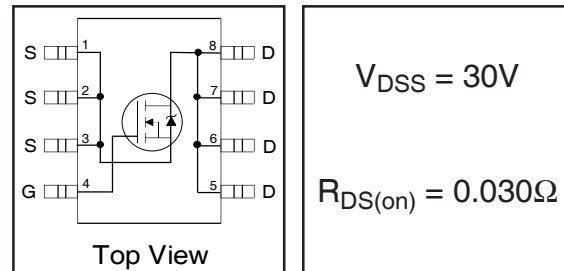


IRF7201PbF

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

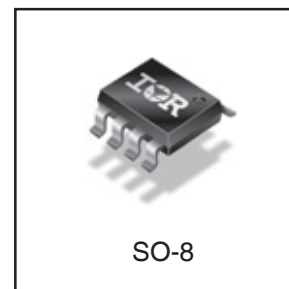
HEXFET® Power MOSFET



Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.3	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.8	
I_{DM}	Pulsed Drain Current ①	58	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.5	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse $tp < 10\mu s$	30	V
E_{AS}	Single Pulse Avalanche Energy ②	70	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

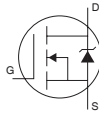
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤	—	50	$^\circ C/W$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.030	Ω	$V_{GS} = 10V, I_D = 7.3A$ ④
		—	—	0.050		$V_{GS} = 4.5V, I_D = 3.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	5.8	—	—	S	$V_{DS} = 15V, I_D = 2.3A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	19	28	nC	$I_D = 4.6A$
Q_{gs}	Gate-to-Source Charge	—	2.3	3.5		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.3	9.5		$V_{GS} = 10V, \text{See Fig. 10}$ ④
$t_{d(on)}$	Turn-On Delay Time	—	7.0	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	35	—		$I_D = 4.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	21	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	19	—		$R_D = 3.2\Omega, \text{See Fig. 9}$ ④
C_{iss}	Input Capacitance	—	550	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	260	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	100	—		$f = 1.0\text{MHz}, \text{See Fig. 9}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	58		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 4.6A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	48	73	ns	$T_J = 25^\circ\text{C}, I_F = 4.6A$
Q_{rr}	Reverse Recovery Charge	—	73	110	nC	$di/dt = 100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 15V$, starting $T_J = 25^\circ\text{C}$, $L = 6.6\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 4.6A$. (See Figure 8)
- ③ $I_{SD} \leq 4.6A, di/dt \leq 120A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ When mounted on 1 inch square copper board, $t < 10\text{sec}$

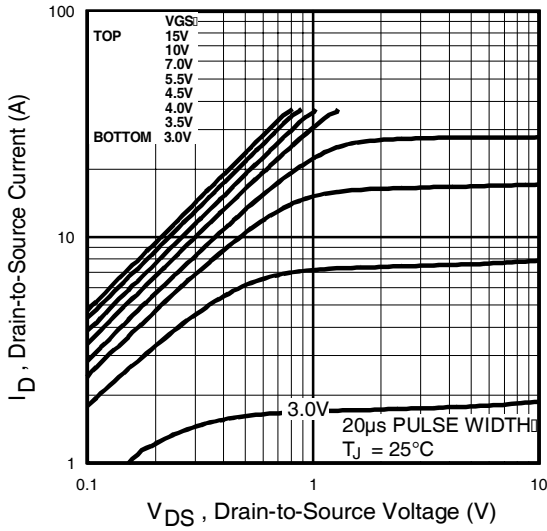


Fig 1. Typical Output Characteristics

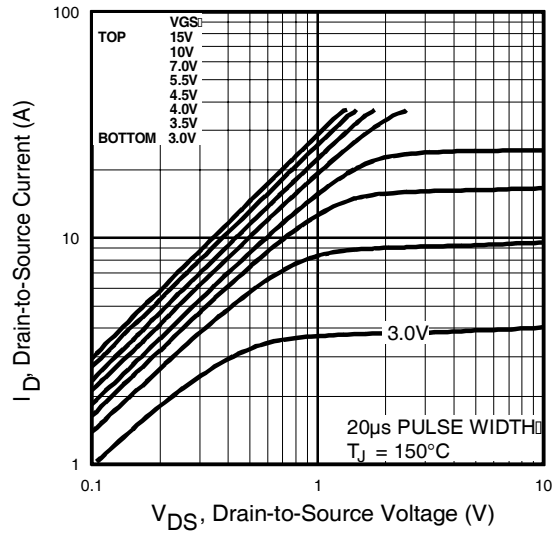


Fig 2. Typical Output Characteristics

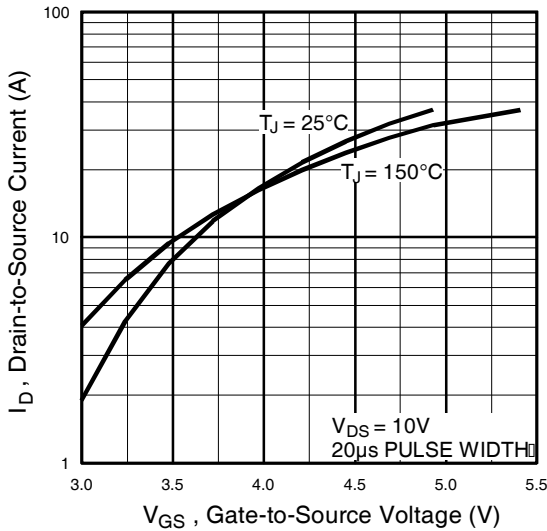


Fig 3. Typical Transfer Characteristics

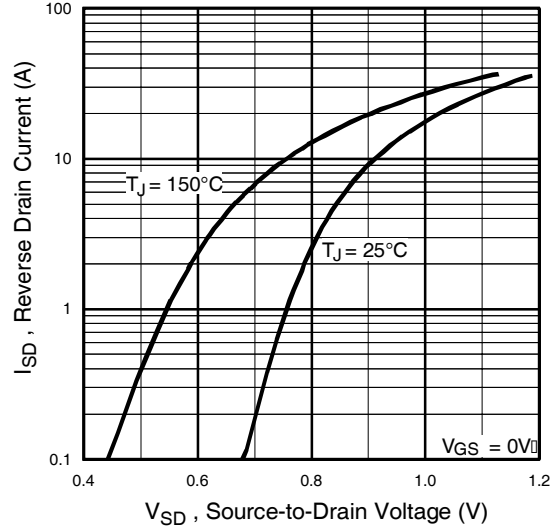


Fig 4. Typical Source-Drain Diode Forward Voltage

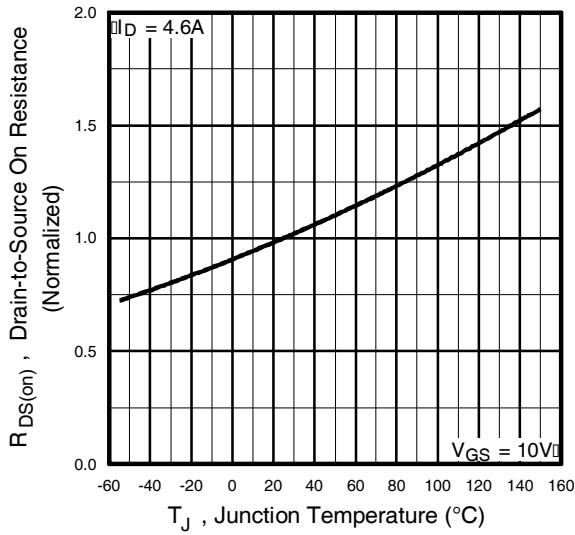


Fig 5. Normalized On-Resistance Vs. Temperature

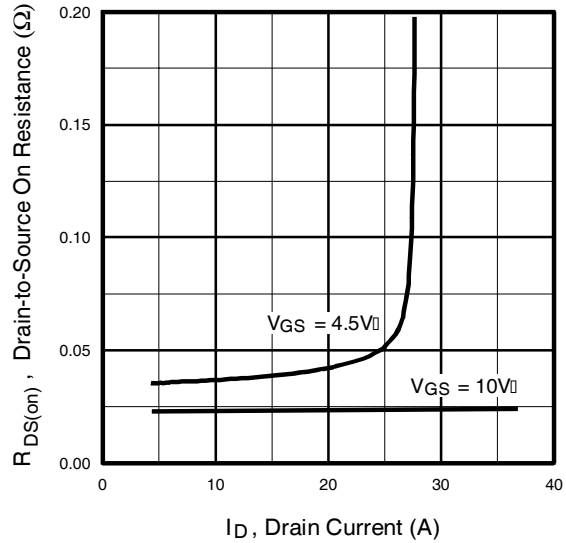


Fig 6. On-Resistance Vs. Drain Current

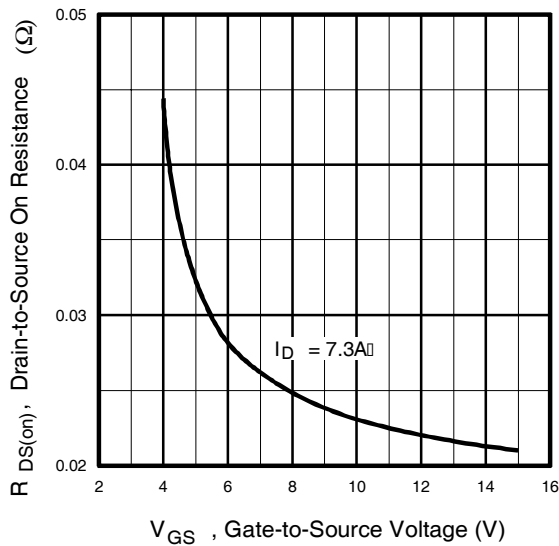


Fig 7. On-Resistance Vs. Gate Voltage

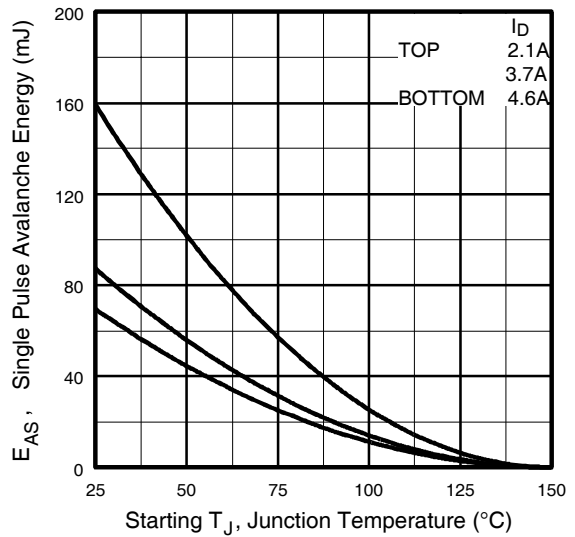


Fig 8. Maximum Avalanche Energy Vs. Drain Current

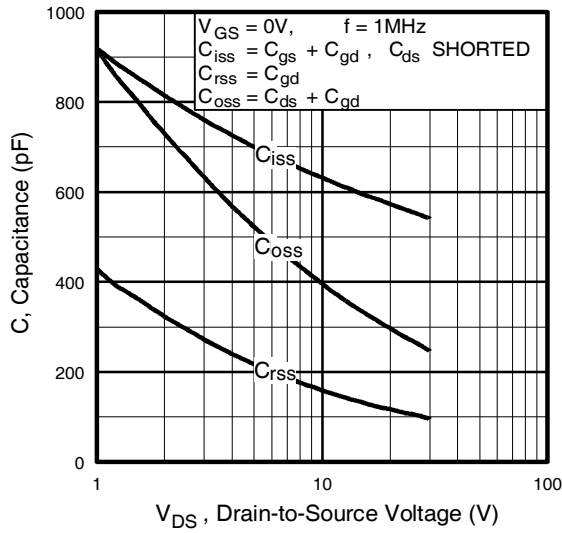


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

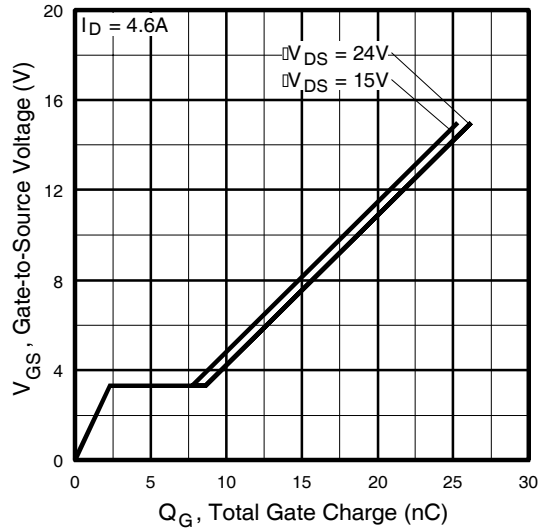


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

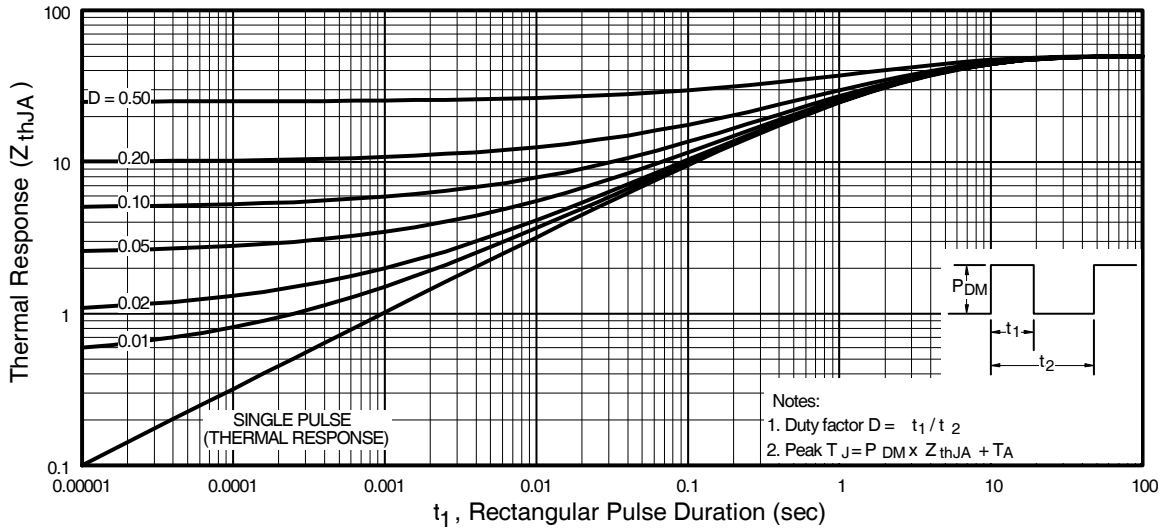
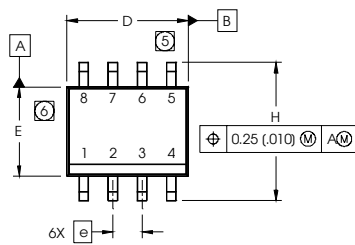


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

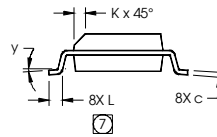
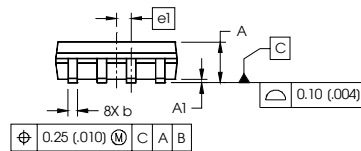
IRF7201PbF

SO-8 Package Outline

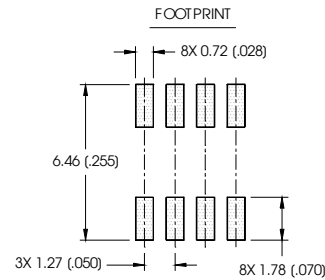
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

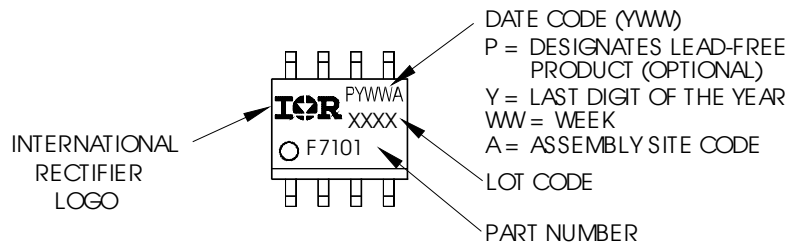


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 - ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
 - ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
 - ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



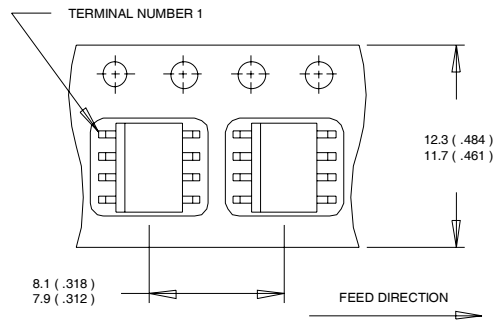
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



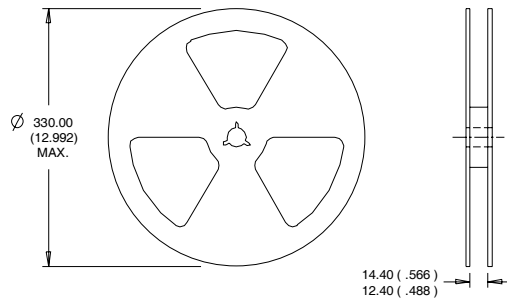
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.

Данный компонент на территории Российской Федерации

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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